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Pinouts

Figure 1. Pin Diagram - 28-Pin CDIP

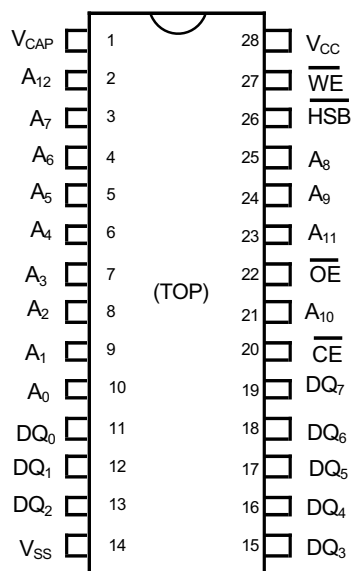
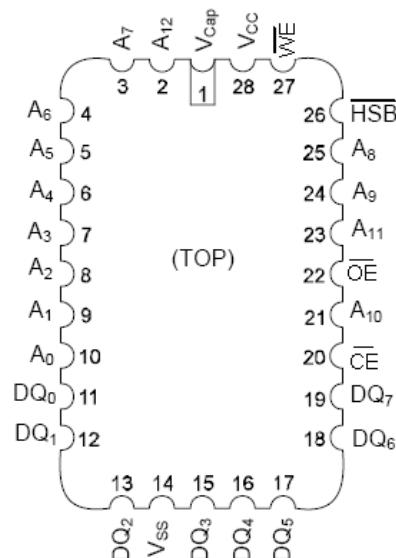


Figure 2. Pin Diagram - 28-Pin LCC



Pin Definitions

Pin Name	Alt	IO Type	Description
A ₀ -A ₁₂		Input	Address Inputs. Used to select one of the 8,192 bytes of the nvSRAM.
DQ ₀ -DQ ₇		Input or Output	Bidirectional Data IO Lines. Used as input or output lines depending on operation.
$\overline{WE}$	$\overline{W}$	Input	Write Enable Input, Active LOW. When the chip is enabled and $\overline{WE}$ is LOW, data on the I/O pins is written to the specific address location.
$\overline{CE}$	$\overline{E}$	Input	Chip Enable Input, Active LOW. When LOW, selects the chip. When HIGH, deselects the chip.
$\overline{OE}$	$\overline{G}$	Input	Output Enable, Active LOW. The active LOW $\overline{OE}$ input enables the data output buffers during read cycles. Deasserting $\overline{OE}$ HIGH causes the I/O pins to tristate.
V _{SS}		Ground	Ground for the Device. The device is connected to ground of the system.
V _{CC}		Power Supply	Power Supply Inputs to the Device.
HSB		Input or Output	Hardware Store Busy (HSB). When LOW, this output indicates a Hardware Store is in progress. When pulled low external to the chip, it initiates a nonvolatile STORE operation. A weak internal pull up resistor keeps this pin high if not connected (connection optional).
V _{CAP}		Power Supply	AutoStore Capacitor. Supplies power to nvSRAM during power loss to store data from SRAM to nonvolatile elements.

Device Operation

The STK12C68-5 nvSRAM is made up of two functional components paired in the same physical cell. These are an SRAM memory cell and a nonvolatile QuantumTrap cell. The SRAM memory cell operates as a standard fast static RAM. Data in the SRAM is transferred to the nonvolatile cell (the STORE operation) or from the nonvolatile cell to SRAM (the RECALL operation). This unique architecture enables the storage and recall of all cells in parallel. During the STORE and RECALL operations, SRAM Read and Write operations are inhibited. The STK12C68-5 supports unlimited reads and writes similar to a typical SRAM. In addition, it provides unlimited RECALL operations from the nonvolatile cells and up to one million STORE operations.

SRAM Read

The STK12C68-5 performs a Read cycle whenever $\overline{CE}$ and OE are LOW while WE and HSB are HIGH. The address specified on pins A_{0-12} determines the 8,192 data bytes accessed. When the Read is initiated by an address transition, the outputs are valid after a delay of t_{AA} (Read cycle 1). If the Read is initiated by CE or OE, the outputs are valid at t_{ACE} or at t_{DOE} , whichever is later (Read cycle 2). The data outputs repeatedly respond to address changes within the t_{AA} access time without the need for transitions on any control input pins, and remains valid until another address change or until $\overline{CE}$ or OE is brought HIGH, or WE or HSB is brought LOW.

SRAM Write

A Write cycle is performed whenever $\overline{CE}$ and $\overline{WE}$ are LOW and HSB is HIGH. The address inputs must be stable prior to entering the Write cycle and must remain stable until either CE or WE goes HIGH at the end of the cycle. The data on the common I/O pins DQ_{0-7} are written into the memory if it has valid t_{SD} , before the end of a WE controlled Write or before the end of an CE controlled Write. Keep OE HIGH during the entire Write cycle to avoid data bus contention on common I/O lines. If OE is left LOW, internal circuitry turns off the output buffers t_{HZWE} after WE goes LOW.

AutoStore Operation

The STK12C68-5 stores data to nvSRAM using one of three storage operations:

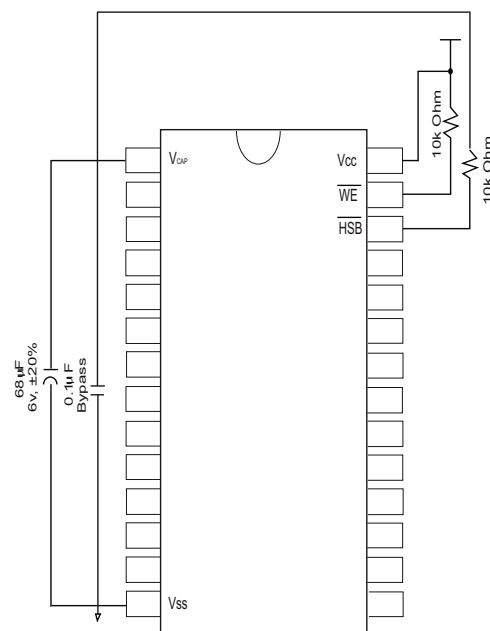
1. Hardware store activated by $\overline{HSB}$
2. Software store activated by an address sequence
3. AutoStore on device power down

AutoStore operation is a unique feature of QuantumTrap technology and is enabled by default on the STK12C68-5.

During normal operation, the device draws current from V_{CC} to charge a capacitor connected to the V_{CAP} pin. This stored charge is used by the chip to perform a single STORE operation. If the voltage on the V_{CC} pin drops below V_{SWITCH} , the part automatically disconnects the V_{CAP} pin from V_{CC} . A STORE operation is initiated with power provided by the V_{CAP} capacitor.

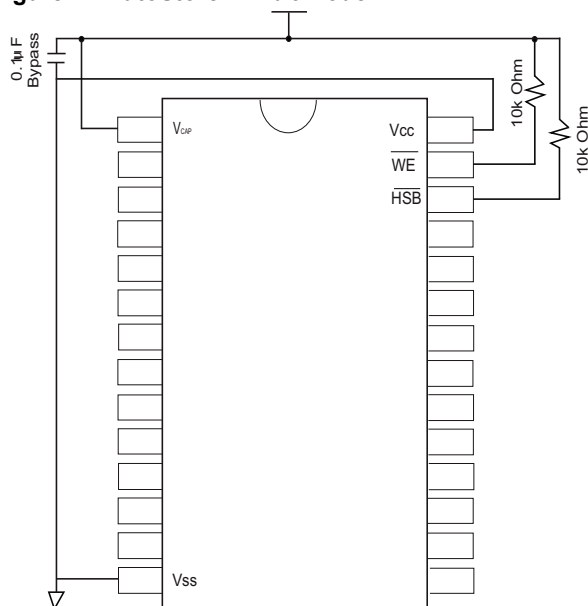
Figure 3 shows the proper connection of the storage capacitor (V_{CAP}) for automatic store operation. A charge storage capacitor between 68 μF and 220 μF ($\pm 20\%$) rated at 6 V must be provided. The voltage on the V_{CAP} pin is driven to 5 V by a charge pump internal to the chip. A pull-up is placed on WE to hold it inactive during power up.

Figure 3. AutoStore Mode



In system power mode, both V_{CC} and V_{CAP} are connected to the +5 V power supply without the 68 μF capacitor. In this mode, the AutoStore function of the STK12C68-5 operates on the stored system charge as power goes down. The user must, however, guarantee that V_{CC} does not drop below 3.6 V during the 10 ms STORE cycle.

To reduce unnecessary nonvolatile stores, AutoStore, and Hardware Store operations are ignored, unless at least one Write operation has taken place since the most recent STORE or RECALL cycle. Software initiated STORE cycles are performed regardless of whether a Write operation has taken place. An optional pull-up resistor is shown connected to HSB. The HSB signal is monitored by the system to detect if an AutoStore cycle is in progress.

Figure 4. AutoStore Inhibit Mode


If the power supply drops faster than 20 $\mu\text{s}/\text{volt}$ before V_{CC} reaches V_{SWITCH} , then a 2.2 Ω resistor must be connected between V_{CC} and the system supply to avoid momentary excess of current between V_{CC} and V_{CAP} .

AutoStore Inhibit Mode

If an automatic STORE on power loss is not required, then V_{CC} is tied to ground and +5 V is applied to V_{CAP} (Figure 4). This is the AutoStore Inhibit mode, where the AutoStore function is disabled. If the STK12C68-5 is operated in this configuration, references to V_{CC} are changed to V_{CAP} throughout this data sheet. In this mode, STORE operations are triggered through software control or the HSB pin. To enable or disable Autostore using an I/O port pin see [Preventing Store on page 6](#). It is not permissible to change between these three options “on the fly”.

Hardware STORE (HSB) Operation

The STK12C68-5 provides the $\overline{\text{HSB}}$ pin for controlling and acknowledging the STORE operations. The $\overline{\text{HSB}}$ pin is used to request a hardware STORE cycle. When the HSB pin is driven LOW, the STK12C68-5 conditionally initiates a STORE operation after t_{DELAY} . An actual STORE cycle only begins if a Write to the SRAM takes place since the last STORE or RECALL cycle. The HSB pin also acts as an open drain driver that is internally driven LOW to indicate a busy condition, while the STORE (initiated by any means) is in progress.

SRAM Read and Write operations, that are in progress when HSB is driven LOW by any means, are given time to complete before the STORE operation is initiated. After HSB goes LOW, the STK12C68-5 continues SRAM operations for t_{DELAY} . During t_{DELAY} , multiple SRAM Read operations take place. If a Write is in progress when HSB is pulled LOW, it allows a time, t_{DELAY} to complete. However, any SRAM Write cycles requested after HSB goes LOW are inhibited until HSB returns HIGH.

During any STORE operation, regardless of how it is initiated, the STK12C68-5 continues to drive the HSB pin LOW, releasing it only when the STORE is complete. After completing the STORE operation, the STK12C68-5 remains disabled until the HSB pin returns HIGH.

If $\overline{\text{HSB}}$ is not used, it is left unconnected.

Hardware RECALL (Power Up)

During power-up or after any low-power condition ($V_{CC} < V_{\text{RESET}}$), an internal RECALL request is latched. When V_{CC} once again exceeds the sense voltage of V_{SWITCH} , a RECALL cycle is automatically initiated and takes t_{HRECALL} to complete.

If the STK12C68-5 is in a Write state at the end of power-up RECALL, the SRAM data is corrupted. To help avoid this situation, a 10 K Ω resistor is connected either between $\overline{\text{WE}}$ and system V_{CC} or between $\overline{\text{CE}}$ and system V_{CC} .

Software STORE

Data is transferred from the SRAM to the nonvolatile memory by a software address sequence. The STK12C68-5 software STORE cycle is initiated by executing sequential $\overline{\text{CE}}$ controlled Read cycles from six specific address locations in exact order. During the STORE cycle, an erase of the previous nonvolatile data is first performed followed by a program of the nonvolatile elements. When a STORE cycle is initiated, input and output are disabled until the cycle is completed.

Because a sequence of Reads from specific addresses is used for STORE initiation, it is important that no other Read or Write accesses intervene in the sequence. If they intervene, the sequence is aborted and no STORE or RECALL takes place.

To initiate the software STORE cycle, the following Read sequence is performed:

1. Read address 0x0000, Valid READ
2. Read address 0x1555, Valid READ
3. Read address 0x0AAA, Valid READ
4. Read address 0x1FFF, Valid READ
5. Read address 0x10F0, Valid READ
6. Read address 0x0F0F, Initiate STORE cycle

The software sequence is clocked with $\overline{\text{CE}}$ controlled Reads or OE controlled Reads. When the sixth address in the sequence is entered, the STORE cycle commences and the chip is disabled. It is important that Read cycles and not Write cycles are used in the sequence. It is not necessary that OE is LOW for a valid sequence. After the t_{STORE} cycle time is fulfilled, the SRAM is again activated for Read and Write operation.

Software RECALL

Data is transferred from the nonvolatile memory to the SRAM by a software address sequence. A software RECALL cycle is initiated with a sequence of Read operations in a manner similar to the software STORE initiation. To initiate the RECALL cycle, the following sequence of $\overline{\text{CE}}$ controlled Read operations is performed:

1. Read address 0x0000, Valid READ
2. Read address 0x1555, Valid READ

3. Read address 0x0AAA, Valid READ
4. Read address 0x1FFF, Valid READ
5. Read address 0x10F0, Valid READ
6. Read address 0x0F0E, Initiate RECALL cycle

Internally, RECALL is a two step procedure. First, the SRAM data is cleared; then, the nonvolatile information is transferred into the SRAM cells. After the t_{RECALL} cycle time, the SRAM is again ready for Read and Write operations. The RECALL operation does not alter the data in the nonvolatile elements. The nonvolatile data can be recalled an unlimited number of times.

Data Protection

The STK12C68-5 protects data from corruption during low-voltage conditions by inhibiting all externally initiated STORE and Write operations. The low-voltage condition is detected when V_{CC} is less than V_{SWITCH} . If the STK12C68-5 is in a Write mode (both $\overline{\text{CE}}$ and $\overline{\text{WE}}$ are low) at power up after a RECALL or after a STORE, the Write is inhibited until a negative transition on $\overline{\text{CE}}$ or $\overline{\text{WE}}$ is detected. This protects against inadvertent writes during power up or brown out conditions.

Noise Considerations

The STK12C68-5 is a high-speed memory. It must have a high frequency bypass capacitor of approximately 0.1 μF connected between V_{CC} and V_{SS} , using leads and traces that are as short as possible. As with all high-speed CMOS ICs, careful routing of power, ground, and signals reduce circuit noise.

Hardware Protect

The STK12C68-5 offers hardware protection against inadvertent STORE operation and SRAM Writes during low-voltage conditions. When $V_{\text{CAP}} < V_{\text{SWITCH}}$, all externally initiated STORE operations and SRAM Writes are inhibited. AutoStore can be completely disabled by tying V_{CC} to ground and applying +5 V to V_{CAP} . This is the AutoStore Inhibit mode; in this mode, STOREs are only initiated by explicit request using either the software sequence or the HSB pin.

Low Average Active Power

CMOS technology provides the STK12C68-5 the benefit of drawing significantly less current when it is cycled at times longer than 50 ns. Figure 5 and Figure 6 shows the relationship between I_{CC} and Read or Write cycle time. Worst case current consumption is shown for both CMOS and TTL input levels (commercial temperature range, $V_{\text{CC}} = 5.5 \text{ V}$, 100% duty cycle on chip enable). Only standby current is drawn when the chip is disabled. The overall average current drawn by the STK12C68-5 depends on the following items:

- The duty cycle of chip enable
- The overall cycle rate for accesses
- The ratio of Reads to Writes
- CMOS versus TTL input levels
- The operating temperature

- The V_{CC} level

- I/O loading

Figure 5. Current Versus Cycle Time (Read)

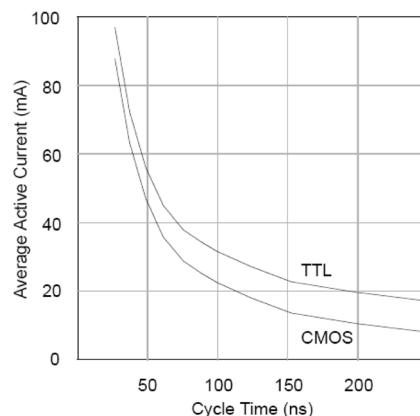
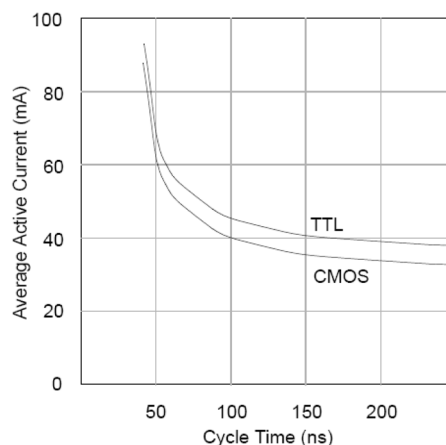


Figure 6. Current Versus Cycle Time (Write)



Preventing Store

The STORE function is disabled by holding $\overline{\text{HSB}}$ high with a driver capable of sourcing 30 mA at a V_{OH} of at least 2.2 V, because it must overpower the internal pull-down device. This device drives $\overline{\text{HSB}}$ LOW for 20 ms at the onset of a STORE. When the STK12C68-5 is connected for AutoStore operation (system V_{CC} connected to V_{CC} and a 68 mF capacitor on V_{CAP}) and V_{CC} crosses V_{SWITCH} on the way down, the STK12C68-5 attempts to pull $\overline{\text{HSB}}$ LOW. If $\overline{\text{HSB}}$ does not actually get below V_{IL} , the part stops trying to pull $\overline{\text{HSB}}$ LOW and aborts the STORE attempt.

Best Practices

nvSRAM products have been used effectively for over 15 years. While ease-of-use is one of the product's main system values, experience gained working with hundreds of applications has resulted in the following suggestions as best practices:

- The nonvolatile cells in an nvSRAM are programmed on the test floor during final test and quality assurance. Incoming inspection routines at customer or contract manufacturer's sites sometimes reprograms these values. Final NV patterns are typically repeating patterns of AA, 55, 00, FF, A5, or 5A. The end product's firmware must not assume that an NV array is in a set programmed state. Routines that check memory content values to determine first time system configuration, cold or warm boot status, and so on must always program a unique NV pattern (for example, complex 4-byte pattern of 46 E6 49 53 hex or more random bytes) as part of the final system manufacturing test to ensure these system routines work consistently.
- Power-up boot firmware routines must rewrite the nvSRAM into the desired state. While the nvSRAM is shipped in a preset state, best practice is to again rewrite the nvSRAM into the desired state as a safeguard against events that might flip the bit inadvertently (program bugs, incoming inspection routines, and so on).
- The V_{CAP} value specified in this datasheet includes a minimum and a maximum value size. The best practice is to meet this requirement and not exceed the maximum V_{CAP} value because the higher inrush currents may reduce the reliability of the internal pass transistor. Customers who want to use a larger V_{CAP} value to make sure there is extra store charge must discuss their V_{CAP} size selection with Cypress.

Table 1. Hardware Mode Selection

$\overline{CE}$	$\overline{WE}$	$\overline{HSB}$	A12–A0	Mode	IO	Power
H	X	H	X	Not Selected	Output High Z	Standby
L	H	H	X	Read SRAM	Output Data	Active ^[3]
L	L	H	X	Write SRAM	Input Data	Active
X	X	L	X	Nonvolatile STORE	Output High Z	I_{CC2} ^[1]
L	H	H	0x0000 0x1555 0x0AAA 0x1FFF 0x10F0 0x0F0F	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Nonvolatile STORE	Output Data Output Data Output Data Output Data Output Data Output High Z	Active I_{CC2} ^[2, 3]
L	H	H	0x0000 0x1555 0x0AAA 0x1FFF 0x10F0 0x0F0E	Read SRAM Read SRAM Read SRAM Read SRAM Read SRAM Nonvolatile RECALL	Output Data Output Data Output Data Output Data Output Data Output High Z	Active ^[2, 3]

Notes

1. HSB STORE operation occurs only if an SRAM Write is done since the last nonvolatile cycle. After the STORE (if any) completes, the part goes into standby mode, inhibiting all operations until HSB rises.
2. The six consecutive addresses must be in the order listed. $\overline{WE}$ must be high during all six consecutive $\overline{CE}$ controlled cycles to enable a nonvolatile cycle.
3. I/O state assumes $\overline{OE} \leq V_{IL}$. Activation of nonvolatile cycles does not depend on state of $\overline{OE}$.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

Storage Temperature -65 °C to +150 °C

Temperature under Bias -55 °C to +125 °C

Voltage on Input Relative to GND.....-0.5 V to 7.0 V

Voltage on Input Relative to V_{SS} -0.6 V to $V_{CC} + 0.5$ V

Voltage on DQ_{0-7} or $\overline{HSB}$ -0.5 V to $V_{CC} + 0.5$ V

Power Dissipation..... 1.0 W

DC output Current (1 output at a time, 1s duration) 15 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Military	-55 °C to +125 °C	4.5 V to 5.5 V

DC Electrical Characteristics

Over the operating range ($V_{CC} = 4.5$ V to 5.5 V) [4]

Parameter	Description	Test Conditions	Min	Max	Unit
I_{CC1}	Average V_{CC} current	$t_{RC} = 35$ ns $t_{RC} = 55$ ns Dependent on output loading and cycle rate. Values obtained without output loads. $I_{OUT} = 0$ mA.	–	75 55	mA mA
I_{CC2}	Average V_{CC} current during STORE	All Inputs Do Not Care, $V_{CC} = \text{Max}$ Average current for duration t_{STORE}	–	3	mA
I_{CC3}	Average V_{CC} current at $t_{RC} = 200$ ns, 5 V, 25 °C Typical	$WE \geq (V_{CC} - 0.2$ V). All other inputs cycling. Dependent on output loading and cycle rate. Values obtained without output loads.	–	10	mA
I_{CC4}	Average V_{CAP} Current during AutoStore Cycle	All Inputs Do Not Care, $V_{CC} = \text{Max}$ Average current for duration t_{STORE}	–	2	mA
I_{SB1} [5]	V_{CC} standby current (Standby, Cycling TTL Input Levels)	$t_{RC} = 35$ ns, $\overline{CE} \geq V_{IH}$ $t_{RC} = 55$ ns, $\overline{CE} \geq V_{IH}$	–	24 19	mA mA
I_{SB2} [5]	V_{CC} standby current	$\overline{CE} \geq (V_{CC} - 0.2$ V). All others $V_{IN} \leq 0.2$ V or $\geq (V_{CC} - 0.2$ V). Standby current level after nonvolatile cycle is complete. Inputs are static. $f = 0$ MHz.	–	2.5	mA
I_{IX}	Input leakage current	$V_{CC} = \text{Max}$, $V_{SS} \leq V_{IN} \leq V_{CC}$	–1	+1	μ A
I_{OZ}	Off state output leakage current	$V_{CC} = \text{Max}$, $V_{SS} \leq V_{IN} \leq V_{CC}$. $\overline{CE}$ or $OE \geq V_{IH}$ or $WE \leq V_{IL}$	–5	+5	μ A
V_{IH}	Input HIGH voltage		2.2	$V_{CC} + 0.5$	V
V_{IL}	Input LOW voltage		$V_{SS} - 0.5$	0.8	V
V_{OH}	Output HIGH voltage	$I_{OUT} = -4$ mA	2.4	–	V
V_{OL}	Output LOW voltage	$I_{OUT} = 8$ mA	–	0.4	V
V_{BL}	Logic '0' voltage on $\overline{HSB}$ output	$I_{OUT} = 3$ mA	–	0.4	V
V_{CAP}	Storage capacitor	Between V_{CAP} pin and V_{SS} , 6 V rated. 68 μ F $\pm 20\%$ nominal	54	260	μ F

Notes

- V_{CC} reference levels throughout this data sheet refer to V_{CC} if that is where the power supply connection is made, or V_{CAP} if V_{CC} is connected to ground.
- $\overline{CE} \geq V_{IH}$ does not produce standby current levels until any nonvolatile cycle in progress has timed out.

Data Retention and Endurance

Parameter	Description	Min	Unit
DATA _R	Data retention	100	Years
NV _C	Nonvolatile STORE operations	1,000	K

Capacitance

In the following table, the capacitance parameters are listed.^[6]

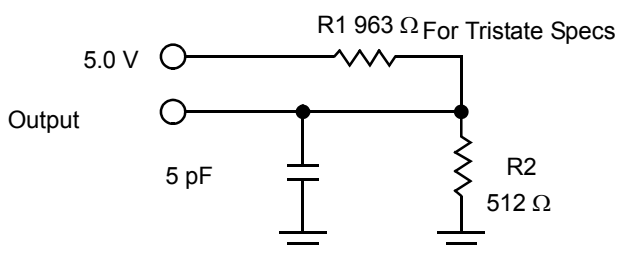
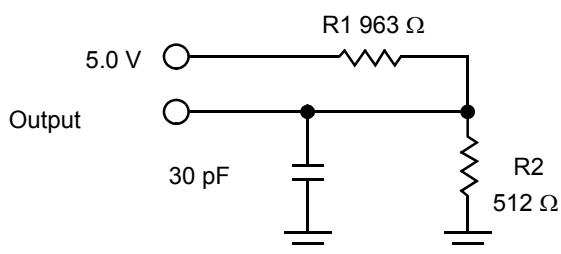
Parameter	Description	Test Conditions	Max	Unit
C _{IN}	Input capacitance	T _A = 25 °C, f = 1 MHz, V _{CC} = 0 to 3.0 V	8	pF
C _{OUT}	Output capacitance		7	pF

Thermal Resistance

In the following table, the thermal resistance parameters are listed.^[6]

Parameter	Description	Test Conditions	28-CDIP	28-LCC	Unit
Θ _{JA}	Thermal resistance (junction to ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA / JESD51.	TBD	TBD	°C/W
Θ _{JC}	Thermal resistance (junction to case)		TBD	TBD	°C/W

Figure 7. AC Test Loads



AC Test Conditions

Input Pulse Levels 0 V to 3 V
 Input Rise and Fall Times (10% to 90%) ≤5 ns
 Input and Output Timing Reference Levels 1.5

Note

6. These parameters are guaranteed by design and are not tested.

AC Switching Characteristics

SRAM Read Cycle

Parameter		Description	35 ns		55 ns		Unit
Cypress Parameter	Alt		Min	Max	Min	Max	
t_{ACE}	t_{ELQV}	Chip enable access time	–	35	–	55	ns
$t_{RC}^{[7]}$	t_{AVAV}, t_{ELEH}	Read cycle time	35	–	55	–	ns
$t_{AA}^{[8]}$	t_{AVQV}	Address access time	–	35	–	55	ns
t_{DOE}	t_{GLQV}	Output enable to data valid	–	15	–	35	ns
$t_{OHA}^{[8]}$	t_{AXQX}	Output hold after address change	5	–	5	–	ns
$t_{LZCE}^{[9]}$	t_{ELQX}	Chip enable to output active	5	–	5	–	ns
$t_{HZCE}^{[9]}$	t_{EHQZ}	Chip disable to output inactive	–	10	–	12	ns
$t_{LZOE}^{[9]}$	t_{GLQX}	Output enable to output active	0	–	0	–	ns
$t_{HZOE}^{[9]}$	t_{GHQZ}	Output disable to output inactive	–	10	–	12	ns
$t_{PU}^{[10]}$	t_{ELICCH}	Chip enable to power active	0	–	0	–	ns
$t_{PD}^{[10]}$	t_{EHICCL}	Chip disable to power standby	–	35	–	55	ns

Switching Waveforms

Figure 8. SRAM Read Cycle 1: Address Controlled ^[7, 8]

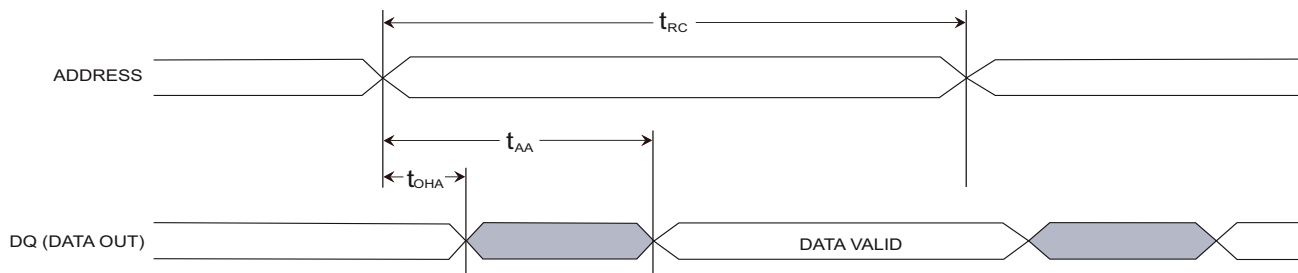
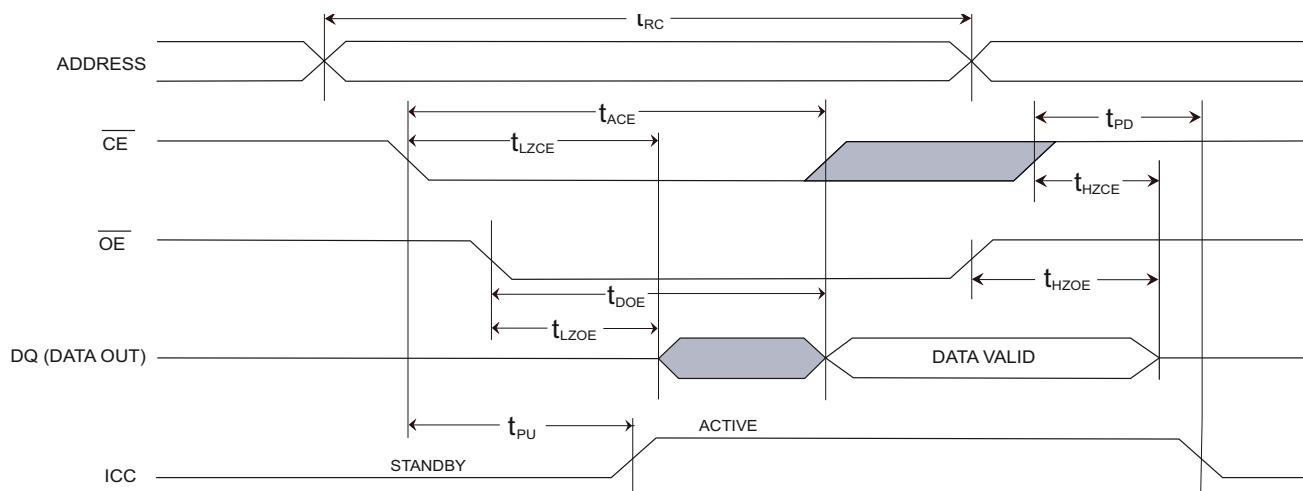


Figure 9. SRAM Read Cycle 2: $\overline{CE}$ and $\overline{OE}$ Controlled ^[7]



Notes

- WE and HSB must be High during SRAM Read cycles.
- Device is continuously selected with $\overline{CE}$ and $\overline{OE}$ both Low.
- Measured ± 200 mV from steady state output voltage.
- These parameters are guaranteed by design and are not tested.

SRAM Write Cycle

Parameter		Description	35 ns		55 ns		Unit
Cypress Parameter	Alt		Min	Max	Min	Max	
t_{WC}	t_{AVAV}	Write cycle time	35	—	55	—	ns
t_{PWE}	t_{WLWH} , t_{WLEH}	Write pulse width	25	—	45	—	ns
t_{SCE}	t_{ELWH} , t_{ELEH}	Chip enable to end of write	25	—	45	—	ns
t_{SD}	t_{DVWH} , t_{DVEH}	Data setup to end of write	12	—	25	—	ns
t_{HD}	t_{WHDX} , t_{EHDX}	Data hold after end of write	0	—	0	—	ns
t_{AW}	t_{AVWH} , t_{AVEH}	Address setup to end of write	25	—	45	—	ns
t_{SA}	t_{AVWL} , t_{AVEL}	Address setup to start of write	0	—	0	—	ns
t_{HA}	t_{WHAX} , t_{EHAX}	Address hold after end of write	0	—	0	—	ns
$t_{HZWE}^{[11,12]}$	t_{WLQZ}	Write enable to output disable	—	13	—	15	ns
$t_{LZWE}^{[11]}$	t_{WHQX}	Output active after end of write	5	—	5	—	ns

Switching Waveforms

Figure 10. SRAM Write Cycle 1: $\overline{WE}$ Controlled [13, 14]

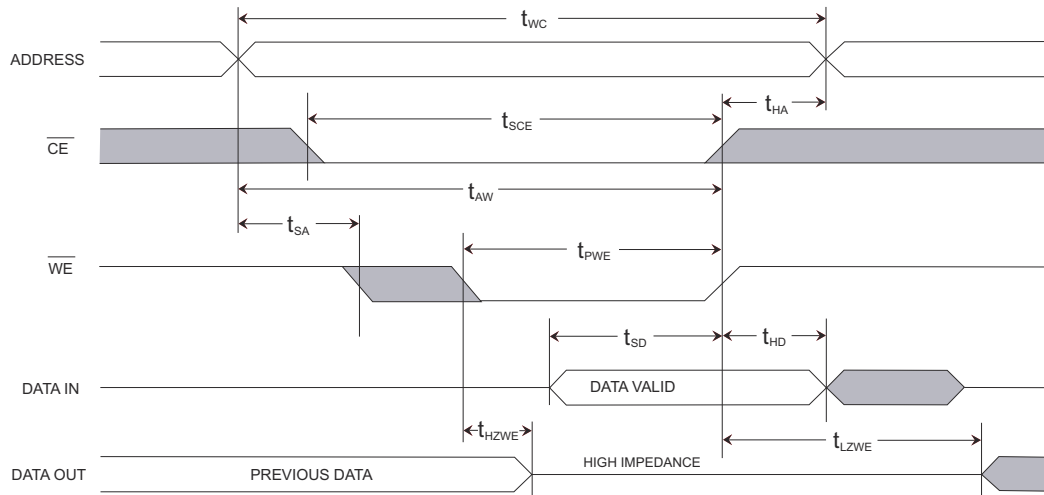
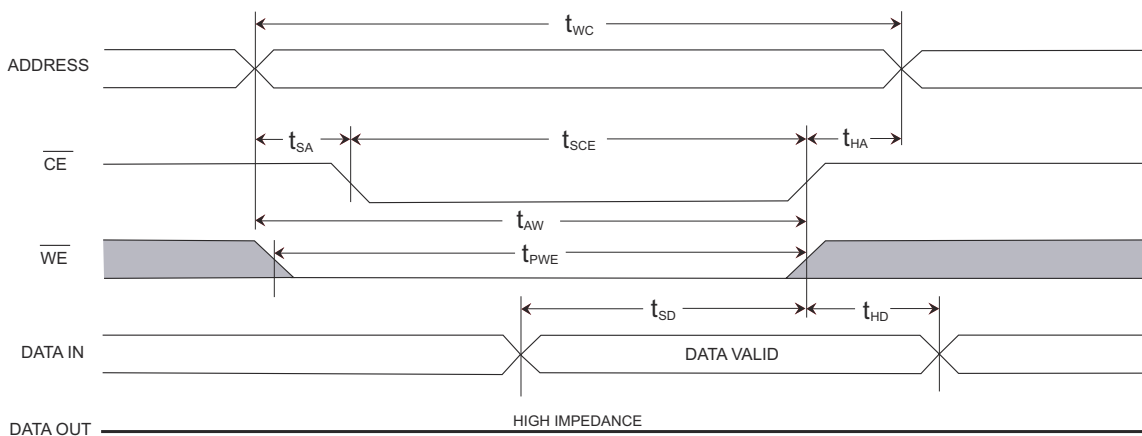


Figure 11. SRAM Write Cycle 2: $\overline{CE}$ Controlled [13, 14]



Notes

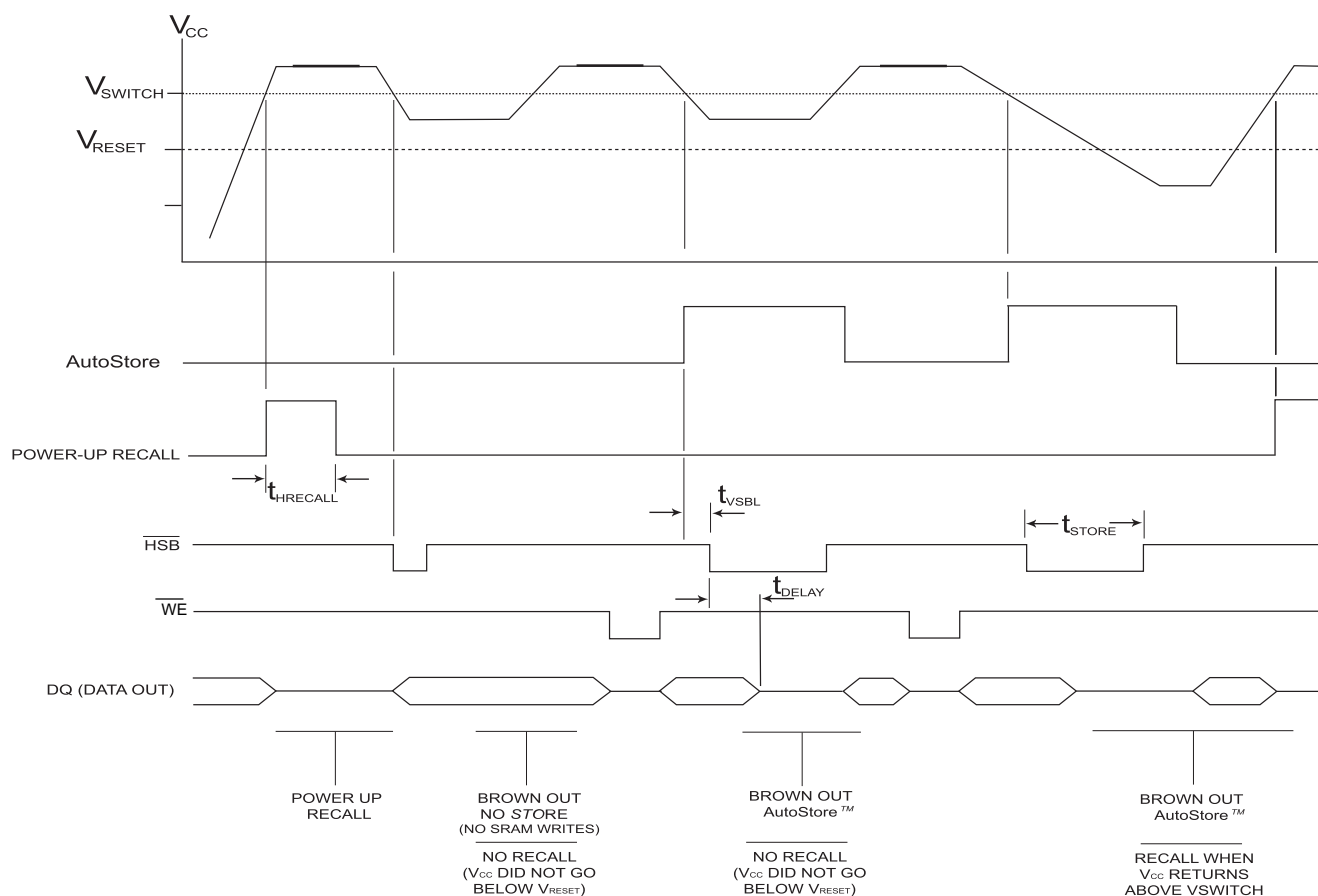
11. Measured ± 200 mV from steady state output voltage.
12. If $\overline{WE}$ is Low when $\overline{CE}$ goes Low, the outputs remain in the high impedance state.
13. HSB must be high during SRAM Write cycles.
14. $\overline{CE}$ or $\overline{WE}$ must be greater than V_{IH} during address transitions.

AutoStore or Power Up RECALL

Parameter	Alt	Description	STK12C68-5		Unit
			Min	Max	
$t_{HRECALL}^{[17]}$	$t_{RESTORE}$	Power up RECALL duration	–	550	μs
$t_{STORE}^{[18, 19, 20]}$	t_{HLHZ}	STORE cycle duration	–	10	ms
$t_{DELAY}^{[15, 19]}$	t_{HLQZ}, t_{BLQZ}	Time allowed to complete SRAM cycle	1	–	μs
V_{SWITCH}		Low voltage trigger level	4.0	4.5	V
V_{RESET}		Low voltage reset level	–	3.9	V
$t_{VCCRRISE}$		V_{CC} rise time	150	–	μs
$t_{VSBL}^{[16]}$		Low voltage trigger (V_{SWITCH}) to HSB Low	–	300	ns

Switching Waveform

Figure 12. AutoStore/Power Up RECALL



Notes

15. Measured ± 200 mV from steady state output voltage.
16. HSB must be high during SRAM Write cycles.
17. $t_{HRECALL}$ starts from the time V_{CC} rises above V_{SWITCH} .
18. $\overline{CE}$ and $\overline{OE}$ low for output behavior.
19. $\overline{CE}$ and $\overline{OE}$ low and $\overline{WE}$ high for output behavior.
20. $\overline{HSB}$ is asserted low for 1 μs when V_{CAP} drops through V_{SWITCH} . If an SRAM Write has not taken place since the last nonvolatile cycle, $\overline{HSB}$ is released and no store takes place.

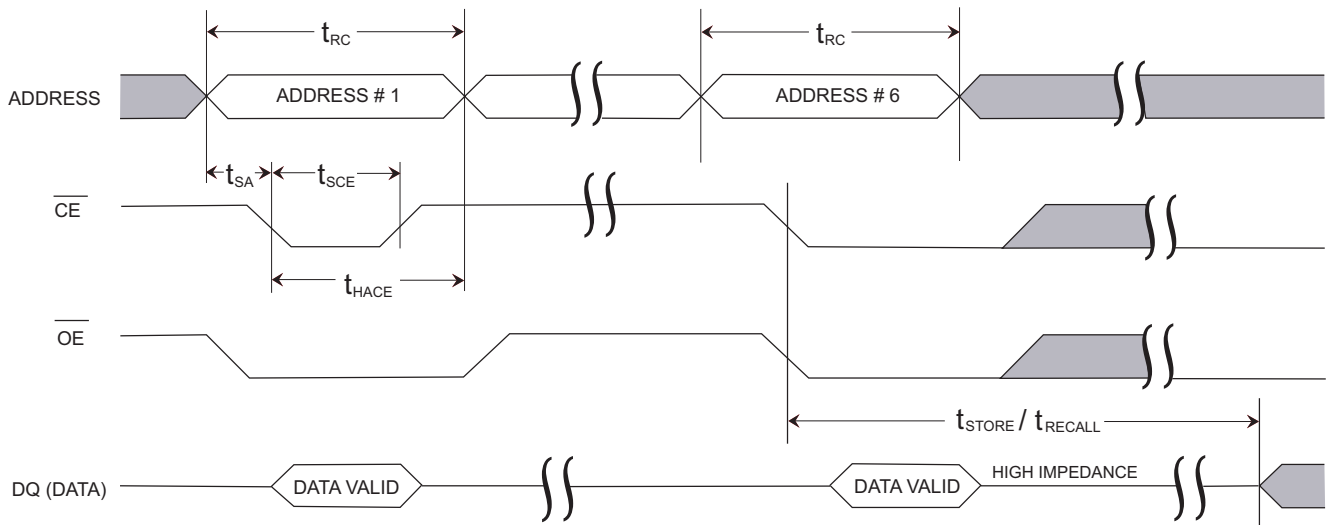
Software Controlled STORE/RECALL Cycle

The software controlled STORE/RECALL cycle follows. ^[23]

Parameter	Alt	Description	35 ns		55 ns		Unit
			Min	Max	Min	Max	
$t_{RC}^{[21]}$	t_{AVAV}	STORE/RECALL initiation cycle time	35	–	55	–	ns
$t_{SA}^{[22]}$	t_{AVEL}	Address setup time	0	–	0	–	ns
$t_{CW}^{[22]}$	t_{ELEH}	Clock pulse width	25	–	30	–	ns
$t_{HACE}^{[22]}$	t_{ELAX}	Address hold time	20	–	20	–	ns
t_{RECALL}		RECALL duration	–	20	–	20	μs

Switching Waveform

Figure 13. $\overline{CE}$ Controlled Software STORE/RECALL Cycle ^[23]



Notes

21. $\overline{CE}$ and $\overline{OE}$ low for output behavior.

22. The software sequence is clocked on the falling edge of $\overline{CE}$ without involving $\overline{OE}$ (double clocking aborts the sequence).

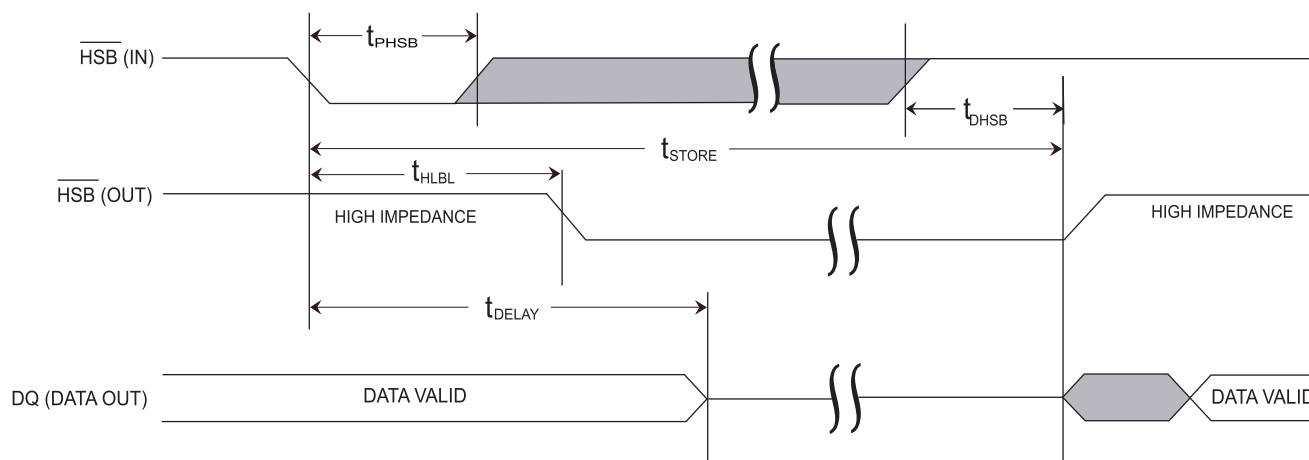
23. The six consecutive addresses must be read in the order listed in Table 1 on page 7. $\overline{WE}$ must be HIGH during all six consecutive cycles.

Hardware STORE Cycle

Parameter	Alt	Description	STK12C68-5		Unit
			Min	Max	
$t_{STORE}^{[25, 26]}$	t_{HLHZ}	STORE cycle duration	–	10	ms
$t_{DHSB}^{[26, 24]}$	$t_{RECOVER}, t_{HHQX}$	Hardware STORE High to inhibit Off	–	700	ns
t_{PHSB}	t_{HLHX}	Hardware STORE pulse width	15	–	ns
t_{HLBL}		Hardware STORE Low to STORE busy	–	300	ns

Switching Waveform

Figure 14. Hardware STORE Cycle

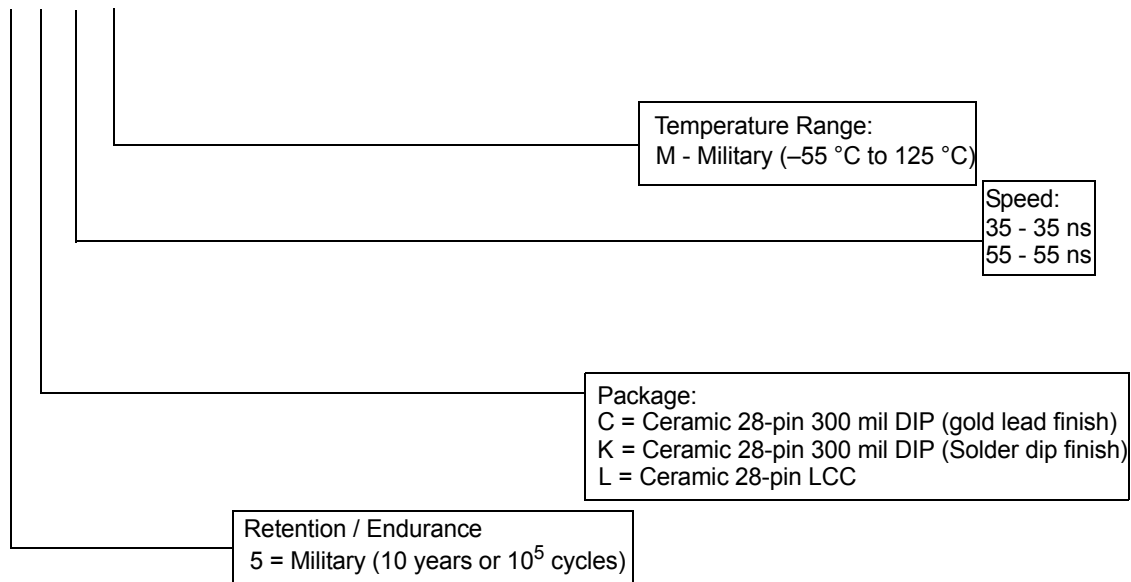


Note

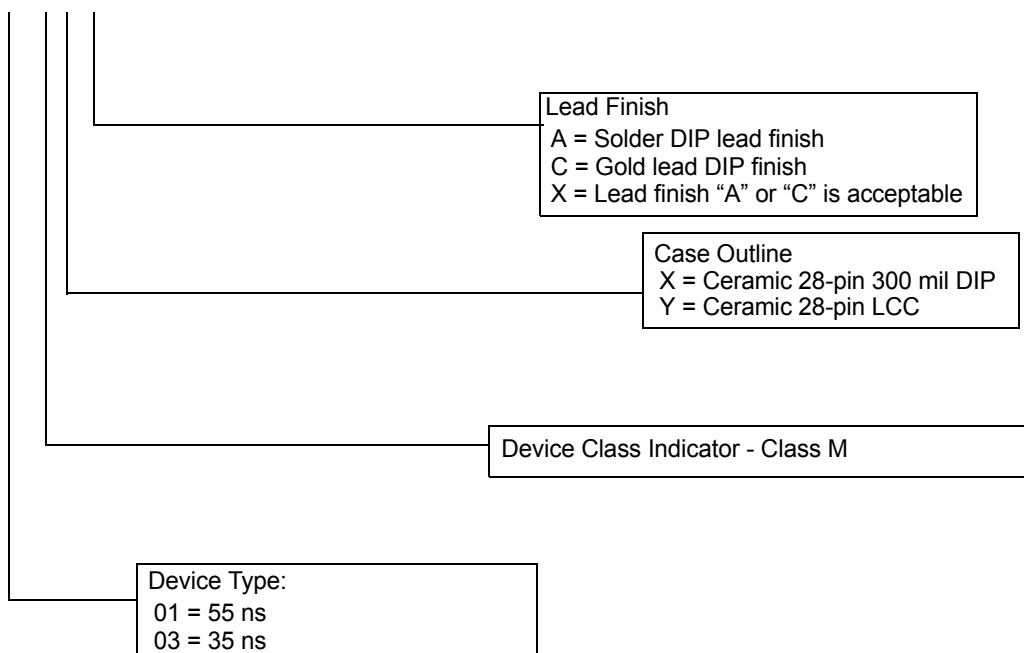
- 24. t_{DHSB} is only applicable after t_{STORE} is complete.
- 25. Measured ± 200 mV from steady state output voltage.
- 26. CE and OE low for output behavior.

Part Numbering Nomenclature

STK12C68 - 5 C 35 M



SMD5962 - 94599 01 MX X



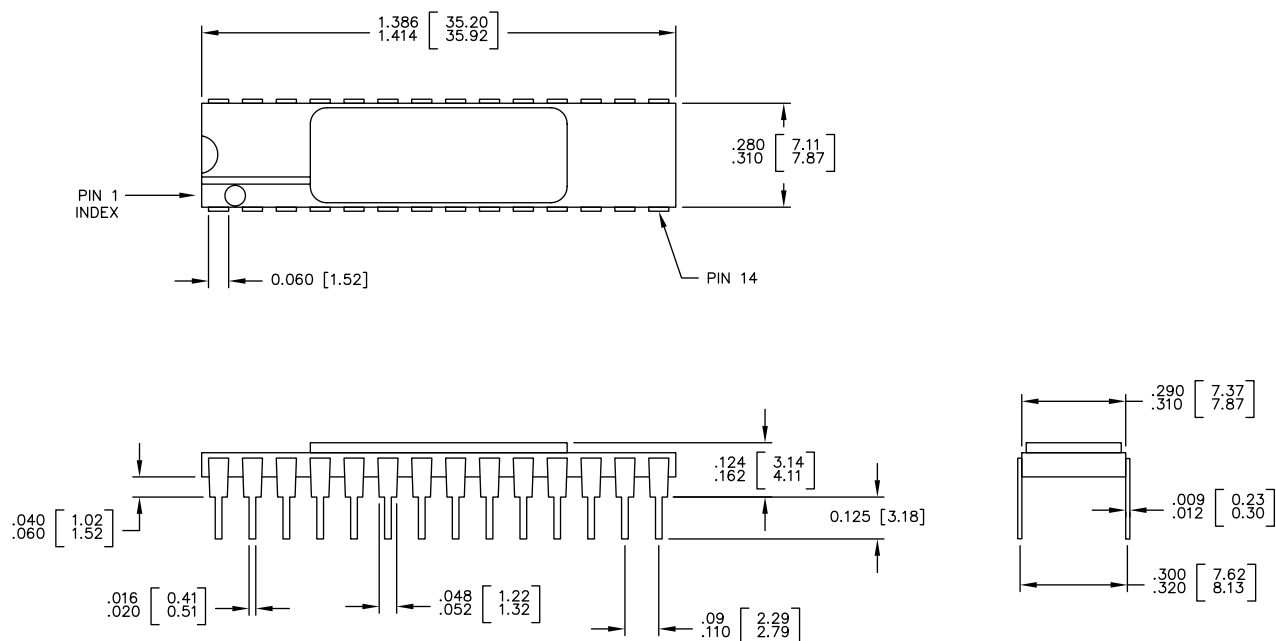
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
35	STK12C68-5C35M	001-51695	28-pin CDIP (300 mil)	Military
	STK12C68-5L35M	001-51696	28-pin LCC (350 mil)	
55	STK12C68-5C55M	001-51695	28-pin CDIP (300 mil)	
	STK12C68-5L55M	001-51696	28-pin LCC (350 mil)	

The above table contains Final information. Contact your local Cypress sales representative for availability of these parts

Package Diagrams

Figure 15. 28-Pin (300-Mil) Side Braze DIP (001-51695)

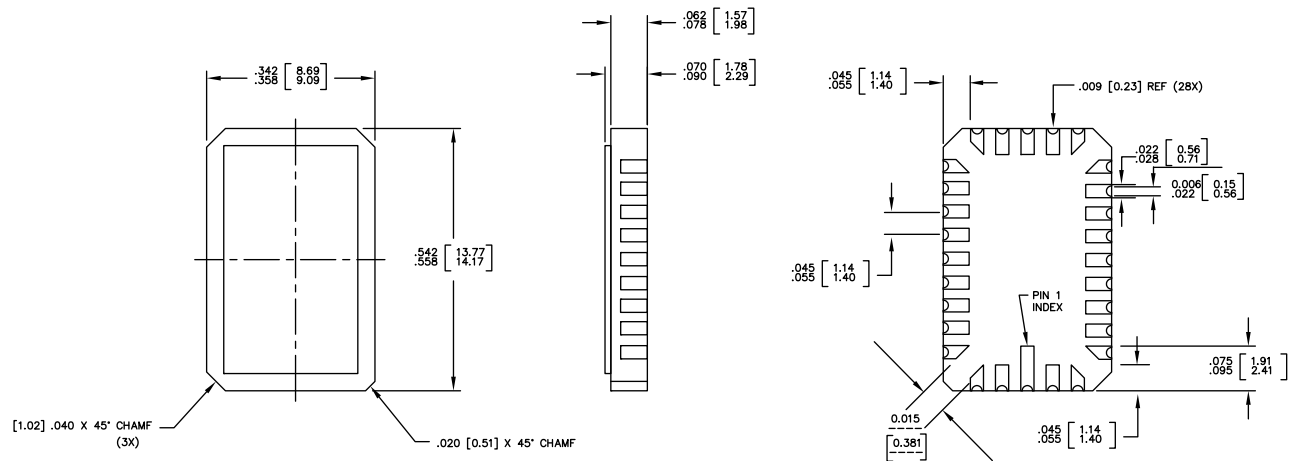


1. ALL DIMENSIONS ARE IN INCHES AND MILLIMETERS [MIN/MAX]
2. PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress Web
3. JEDEC REFERENCE : MO-058

001-51695 *C

Package Diagrams (continued)

Figure 16. 28-Pad (350-Mil) LCC (001-51696)



1. ALL DIMENSION ARE IN INCHES AND MILLIMETERS [MIN/MAX]
2. JEDEC 95 OUTLINE# MO-041
3. PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress Web

001-51696 *C

Acronyms

Acronym	Description
CE	chip enable
CMOS	complementary metal oxide semiconductor
I/O	input/output
nvSRAM	nonvolatile static random access memory
OE	output enable
SRAM	static random access memory
TTL	transistor-transistor logic
WE	write enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degrees Celsius
kΩ	kilohm
μA	microampere
mA	milliampere
μF	microfarad
μs	microsecond
ms	millisecond
ns	nanosecond
pF	picofarad
V	volt
Ω	ohm
W	watt

Document History Page

Document Title: STK12C68-5 (SMD5962-94599), 64 Kbit (8 K x 8) AutoStore nvSRAM Document Number: 001-51026				
Rev	ECN No.	Orig. of Change	Submission Date	Description of Change
**	2666844	GVCH/PYRS	03/02/09	New datasheet
*A	3528539	GVCH	02/17/2012	Added Acronyms, Document Conventions, and Table of Contents. Updated Package Diagrams 001-51695 (from Rev ** to *A) and 001-51696 (from Rev ** to *A). Completing sunset review.
*B	4568935	GVCH	11/14/2014	Added documentation related hyperlink Removed 02 pruned parts - STK12C68-5K35M, STK12C68-5K55M Updated package diagram - 001-51695*A to 001-51695*B and 001-51696*A to 001-51696*B
*C	4706588	GVCH	04/02/2015	Updated package diagrams from 001-51695*B to 001-51695*C and 001-51696*B to 001-51696*C

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